



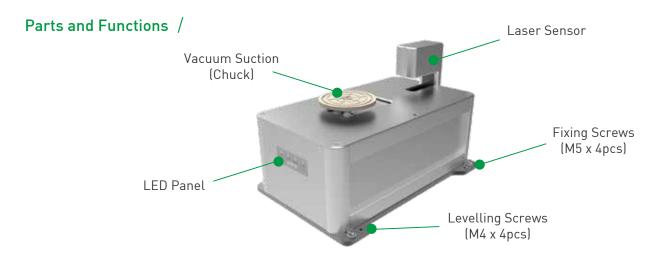




Features /

- HPA series is a three-axis controlled wafer aligner, utilizing HIWIN mechatronic components for high speed, high precision and high efficiency.
- Integrated controller. External controller and cables are not needed, saving space and reducing design complexity.
- Equipped with a smart light-transmitting laser sensor that can support the profile detection function of transparent, translucent and opaque objects, it is applicable for wafers and glass with diameters in 2 inch~12 inch.
- Cleanliness level of the product is Class 1, suitable for applications in semiconductor and photonics.
- ullet Wafer aligning, wafer centering, angle corrections and maintaining a centering repeatability of \pm 0.1mm can be completed under 5 seconds.
- In compliance with relevant safety regulations and directives, the equipment provides a Category 0 stop function. It is recommended to integrate a safety circuit and various functional real-time monitoring modules such as motor control systems, sensing systems, and vacuum systems, ...etc with a system integration partner to offer users the most comprehensive and secure protection.
- Emergency Stop Function: Please use the external emergency stop circuit to cut off the power supply of the input side.
- User friendly design. Status indicators on the equipment exterior allowing user to monitor the status in real time.
- HIWIN's Wafer Aligner has obtained RoHS2 certification, and uses WGK1-compliant grease and NBSK-compliant environmentally friendly packaging.



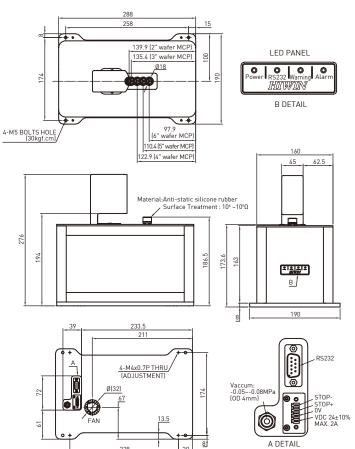


Specifications and Dimensions-HPA Series /

HPA26

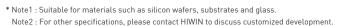
Item	Specifications		
110111	'		
Model	2", 3", 4", 5", 6" shared type		
Model Number		HPA26	
Wafer Size	2", 3", 4", 5", 6"		
Wafer Material	Transparent, Translucent, Opaque* _{Note1}		
Wafer Features	Flat / Notch (SEMI Standard)		
Wafer Thickness	0.4~0.8 mm*Note2		
Wafer Warpage	<±0.1 mm*Note2		
Number of Motion Axis	3-axis (Χ, Υ, θ)		
Wafer Handling Method	Vacuum Suction (Chuck)		
	Χ	56 mm	
Working Range	Υ	\pm 10 mm	
	θ	Continuous	
Allowable Wafer Offset		\pm R4 mm	
Accuracy	Centering $< \pm 0.1 \text{ mm}$		
(RP=Ave+3 σ)	Notch Angle < ± 0.2°		
Communication Protocol	RS232		
Cleanliness Level	Class 1		
D 6 1	Voltage	DC 24V ± 10%	
Power Supply	Current	Max. 2A	
Safety Circuit	After disconnected, the stop activates.		
-	Tube size	Ø4 mm	
Vacuum	Pressure	-0.05~-0.08 MPa	
	Flow	10 L/min (ANR)	
Ambient Temperature	5~40°C		
Ambient Humidity	30~65% (No condensation)		
Weight	6 kg		
Size	L288 mm x W190 mm x H276 mm		

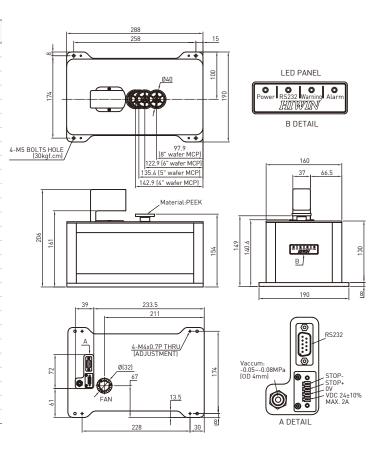




НРД48

Item	Specifications		
Model	4", 5", 6", 8" shared type		
Model Number	HPA48		
Wafer Size		4", 5", 6", 8"	
Wafer Material	Transparent, Translucent, Opaque*Note1		
Wafer Features	Flat / Notch (SEMI Standard)		
Wafer Thickness		0.4~0.8 mm*Note2	
Wafer Warpage	< ± 0.1 mm*Note2		
Number of Motion Axis	3-axis (X, Y, θ)		
Wafer Handling Method	Vacuum Suction (Chuck)		
	X	63 mm	
Working Range	Y	±10 mm	
	θ Continuous		
Allowable Wafer Offset	4 inch: \pm R5 mm ; 5, 6 inch: \pm R8 mm ; 8 inch: \pm R10 mm		
Accuracy	Centering $< \pm$ 0.1 mm		
(RP=Ave+3 σ)	Notch Angle < ± 0.2°		
Communication Protocol	RS232		
Cleanliness Level	Class 1		
Power Supply	Voltage	DC 24V ± 10%	
1 ower Supply	Current	Max. 2A	
Safety Circuit	After disconnected, the stop activates.		
	Tube size	Ø4 mm	
Vacuum	Pressure	-0.05~-0.08 MPa	
	Flow 10 L/min (ANR)		
Ambient Temperature	5~40°C		
Ambient Humidity	30~65% (No condensation)		
Weight	5.8 kg		
Size	L288 mm x W190 mm x H206 mm		

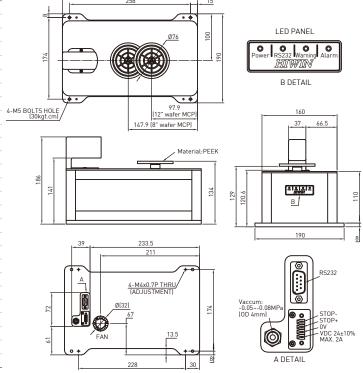




Specifications and Dimensions-HPA Series /

HPA812

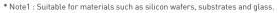
ltem		Considirations	
	Specifications		
Model	8", 12" shared type		
Model Number	HPA812		
Wafer Size		8", 12"	
Wafer Material	Transparent, Translucent, Opaque *Note1		
Wafer Features	Flat / Notch (SEMI Standard)		
Wafer Thickness	0.4~0.8 mm * _{Note2}		
Wafer Warpage		<±0.1 mm *Note2	
Number of Motion Axis	3-axis (X \ Y \ θ)		
Wafer Handling Method	Vacuum Suction (Chuck)		
-	Χ	70 mm	
Working Range	Υ	±10 mm	
	θ	Continuous	
Allowable Wafer Offset	± R10 mm		
Accuracy	Centering $< \pm$ 0.1 mm		
(RP=Ave+3 σ)	Notch Angle < ± 0.2°		
Communication Protocol	RS232		
Cleanliness Level	Class 1		
Power Supply	Voltage	DC 24V \pm 10%	
rower supply	Current	Max. 2A	
Safety Circuit	After disconnected, the stop activates.		
	Tube size	Ø4 mm	
Vacuum	Pressure	-0.05~-0.08 MPa	
	Flow 10 L/min (ANR)		
Ambient Temperature	5~40 °C		
Ambient Humidity	30~65% (No condensation)		
Weight	5.5 kg		
Size	L288 mm x W190 mm x H186 mm		



Specifications and Dimensions-HPA-W Series (Warped wafer) /

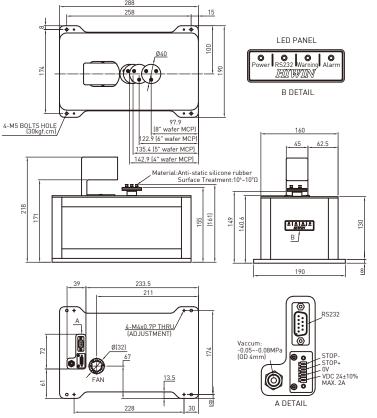
HPA48-W

lt		C:::	
Item	Specifications		
Model	4", 5", 6", 8" shared type		
Model Number	HPA48-W		
Wafer Size		4", 5", 6", 8"	
Wafer Material	Transparent, Translucent, Opaque*Note1		
Wafer Features	Flat / Notch (SEMI Standard)		
Wafer Thickness	0.4~0.8 mm* _{Note} 2		
Wafer Warpage	< ± 1.5 mm (Difference of Height < 3mm)*Note2		
Number of Motion Axis	3-axis (X \ Y \ θ)		
Wafer Handling Method	Vacuum Suction (Chuck)		
	Χ	63 mm	
Working Range	Υ	±10 mm	
	θ Continuous		
Allowable Wafer Offset	±R5 mm		
Accuracy*Note3	Centering	$< \pm$ 0.1 mm	
(RP=Ave+3 σ)	Notch Angle < ± 0.2°		
Communication Protocol	RS232		
Cleanliness Level	Class 1		
Power Supply	Voltage	DC 24V \pm 10%	
1 ower Supply	Current	Max. 2A	
Safety Circuit	After disconnected, the stop activates.		
	Tube size	Ø4 mm	
Vacuum	Pressure	-0.05~-0.08 MPa	
	Flow 10 L/min (ANR)		
Ambient Temperature	5~40°C		
Ambient Humidity	30~65% (No condensation)		
Weight	6.3 kg		
Size	L288 mm x W190 mm x H218 mm		



 $Note 2: For \ other \ specifications, \ please \ contact \ HIWIN \ to \ discuss \ customized \ development.$

Note3 : This data is measured by dummy wafer, if there are other products, please contact HIWIN.



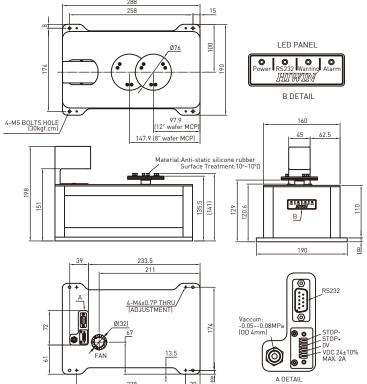
^{*} Note1 : Suitable for materials such as silicon wafers, substrates and glass.

 $Note 2: For \ other \ specifications, \ please \ contact \ HIWIN \ to \ discuss \ customized \ development.$

Specifications and Dimensions-HPA-W Series (Warped wafer) /

HPΔ812-W

ltem	Specifications		
Model	8", 12" shared type		
Model Number	HPA812-W		
Wafer Size		8", 12"	
Wafer Material	Transparer	nt, Translucent, Opaque *Note1	
Wafer Features	Flat / Notch (SEMI Standard)		
Wafer Thickness	0.4~0.8 mm* _{Note2}		
Wafer Warpage	$< \pm 1.5$ mm (Difference of Height < 3 mm)* $_{Note2}$		
Number of Motion Axis	3-axis (X \ Y \ θ)		
Wafer Handling Method	Vacuum Suction (Chuck)		
	Х	70 mm	
Working Range	Υ	±10 mm	
	θ	Continuous	
Allowable Wafer Offset	± R10 mm		
Accuracy*Note3	Centering	$<\pm$ 0.1 mm	
(RP=Ave+3 σ)	Notch Angle	< ± 0.2°	
Communication Protocol	RS232		
Cleanliness Level	Class 1		
Power Supply	Voltage	DC 24V \pm 10%	
rower Supply	Current	Max. 2A	
Safety Circuit	After disconnected, the stop activates.		
	Tube size	Ø4 mm	
Vacuum	Pressure	-0.05~-0.08 MPa	
	Flow	10 L/min (ANR)	
Ambient Temperature	5~40 °C		
Ambient Humidity	30~65% (No condensation)		
Weight	6 kg		
Size	L288 mm x W190 mm x H198 mm		



^{*} Note1 : Suitable for materials such as silicon wafers, substrates and glass.

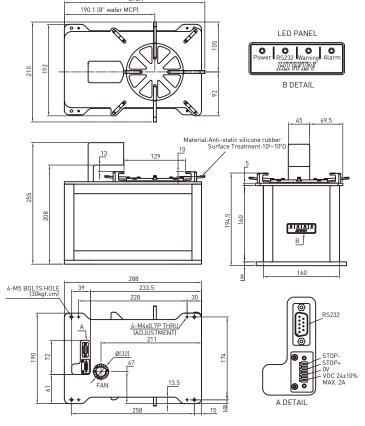
Specifications and Dimensions-HPA-E Series (Edge handling) /

НРА8-Е

Item	Cunnifications		
	Specifications		
Model	8"		
Model Number		HPA8-E	
Wafer Size		8"	
Wafer Material	Transparent, Translucent, Opaque*Note1		
Wafer Features	Notch (SEMI Standard)		
Wafer Thickness	0.4~0.8 mm* _{Note2}		
Wafer Warpage	<±0.1 mm *Note2		
Number of Motion Axis	3-axis (X \ Z \ θ)		
Wafer Handling Method	Edge Contact		
	Χ	8 mm	
Working Range	Z	15.5 mm	
	θ	Continuous	
Allowable Wafer Offset	± R4 mm		
Accuracy	Centering	$< \pm$ 0.1 mm	
(RP=Ave+3 σ)	Notch Angle	< ± 0.2°	
Communication Protocol	RS232		
Cleanliness Level	Class 1		
Danier Committee	Voltage	DC 24V ± 10%	
Power Supply	Current	Max. 2A	
Safety Circuit	After disconnected, the stop activates.		
Ambient Temperature	5~40 °C		
Ambient Humidity	30~65% (No condensation)		
Weight	6.3 kg		
Size	L295.1 mm x W210 mm x H255 mm		

^{*} Note1 : Suitable for materials such as silicon wafers, substrates and glass.

Note2 : For other specifications, please contact HIWIN to discuss customized development.



 $^{{\}tt Note 2: For\ other\ specifications,\ please\ contact\ HIWIN\ to\ discuss\ customized\ development.}$

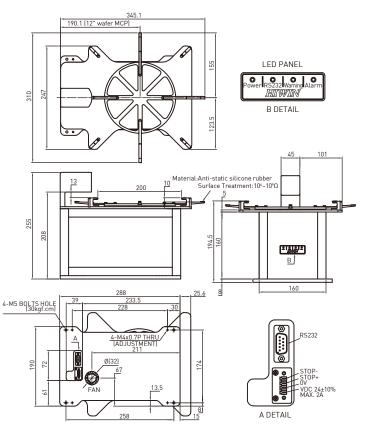
 $Note 3: This \ data \ is \ measured \ by \ dummy \ wafer, if there \ are \ other \ products, \ please \ contact \ HIWIN.$

Specifications and Dimensions-HPA-E Series (Edge handling) /

HPA12-E

ltem	Specifications		
Model	12"		
Model Number	HPA12-E		
Wafer Size		12"	
Wafer Material	Transparent, Translucent, Opaque*Note1		
Wafer Features	Notch (SEMI Standard)		
Wafer Thickness	0.4~0.8 mm* _{Note2}		
Wafer Warpage	<±0.1 mm* _{Note2}		
Number of Motion Axis	3-axis (X \ Z \ θ)		
Wafer Handling Method	Edge Contact		
	Χ	8 mm	
Working Range	Z	15.5 mm	
	θ	Continuous	
Allowable Wafer Offset	± R4 mm		
Accuracy	Centering	$<\pm$ 0.1 mm	
(RP=Ave+3 σ)	Notch Angle	< ± 0.2°	
Communication Protocol	RS232		
Cleanliness Level	Class 1		
Power Supply	Voltage	DC 24V \pm 10%	
Fower Supply	Current	Max. 2A	
Safety Circuit	After disconnected, the stop activates.		
Ambient Temperature	5~40 °C		
Ambient Humidity	30~65% (No condensation)		
Weight	6.4 kg		
Size	L345.1 mm x W310 mm x H255 mm		





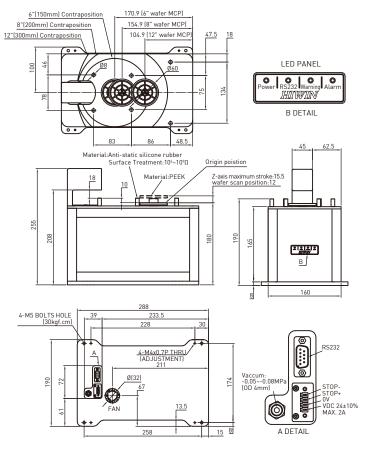
Specifications and Dimensions-HPA-S Series (Stand-alone) /

HPA612-S

Item	Specifications		
Model	6", 8", 12" shared type		
Model Number	HPA612-S		
Wafer Size	6", 8", 12"		
Wafer Material	Transparent, Translucent, Opaque *Note1		
Wafer Features	Flat / Notch (SEMI Standard)		
Wafer Thickness	0.4~0.8 mm*Note2		
Wafer Warpage	< ± 0.1 mm *Note2		
Number of Motion Axis	3-axis (X \ Z \ θ)		
Wafer Handling Method	Vacuum Suction (Chuck)		
	Χ	75 mm	
Working Range	Z	15.5 mm	
	θ	Continuous	
Allowable Wafer Offset	± R4 mm		
Accuracy	Centering $< \pm$ 0.1 mm		
(RP=Ave+3 σ)	Notch Angle < ± 0.2°		
Communication Protocol	RS232		
Cleanliness Level	Class 1		
Power Supply	Voltage	DC 24V \pm 10%	
rower Supply	Current	Max. 2A	
Safety Circuit	After disconnected, the stop activates.		
	Tube size	Ø4 mm	
Vacuum	Pressure	-0.05~-0.08 MPa	
	Flow	10 L/min (ANR)	
Ambient Temperature	5~40 °C		
Ambient Humidity	30~65% (No condensation)		
Weight	6.3 kg		
Size	L288 mm x W190 mm x H255 mm		

^{*} Note1 : Suitable for materials such as silicon wafers, substrates and glass.

Note2 : For other specifications, please contact HIWIN to discuss customized development.



Model Selection Requirement Table

Company Name		Date		
Contact		Tel		
E-Mail		Fax		
Address				
Pre-selected Model Number				
Wafer Size	☐ 2 inch(50mm) ☐ 3 inch(75mm) ☐ 4 inch(100mm) ☐ 5 inch(125mm) ☐ 6 inch(150mm) ☐ 8 inch(200mm) ☐ 12 inch(300mm) ☐ 0thers:			
Wafer Thickness	Wafer Thickness: mm : Wafer Maximum Warpage: mm			
Wafer Features	□ None □ Notch □ Flat □ Double-flat □ Others:			
Wafer Material	☐ Wafer ☐ Glass ☐ Sapphire Substrate ☐ Others:			
Wafer Loading Method	□ Vacuum □ Edge handling □ Others:			
Wafer Contact Material	\square PEEK(Standard) \square PEEK_ESD(10 ⁶ ~10 ⁹ Ω) \square Aluminum \square Others:			
Accuracy Requirements				
Alignment Time				
Communication Method	☐ Serial communication (RS232) ☐ Others:			
Usage Environment	☐ Clean Room ISO Class: ☐ ☐ Dust IP:X ☐ Water IP: X ☐ High Temperature°C ☐ Low Temperature ☐ Others:			
Application Method/Process				
Remark				

Standard Items /

- Wafer Aligner unit: A total of 1 unit
- Power and stop connector: A total of 1 unit (Pin definitions: 24V, 0V, STOP+, STOP-)
- RS232 cable: A total of 1 cable (DB9-F connector on both ends, dual magnetic clasps, cable length 3 meters)
- Anti-static silicone rubber pads (back glue included): Eight pirces in total (HPA-E type only)
- Anti-static silicone rubber washers (back glue included): Six pirces in total (HPA-S type only)





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